



SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATIONATTY. DOCKET NO.  
57810-076SERIAL NO.  
10/663,714APPLICANT  
Daijiro INOUE, et al.

(PTO-1449)

FILING DATE  
September 17, 2003GROUP  
2811 2826

## U.S. PATENT DOCUMENTS

| EXAMINER'S INITIALS | CITE NO. | Document Number<br>Number-Kind Code <sup>2</sup> (if known) | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant<br>Passages or Relevant Figures Appear |
|---------------------|----------|---|--------------------------------|---|--|
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |
|                     |          | US  |                                |   |  |

## FOREIGN PATENT DOCUMENTS

| EXAMINER'S INITIALS | CITE NO. | Foreign Patent Document<br>Country Codes - Number - Kind<br>Codes (if known) | Publication Date<br>MM-DD-YYYY | Name of Patentee or Applicant<br>of Cited Document | Pages,<br>Columns,<br>Lines Where<br>Relevant<br>Figures<br>Appear | Translation                |    |
|---------------------|----------|--|--------------------------------|--|--|----------------------------|----|
|                     |          |  |                                |  |  | Yes                        | No |
| LS                  |          | JP 2001-60720 A  | 03/06/2001                     | TOSHIBA CORP.                                      |  | JAPAN (w/English Abstract) |    |
|                     |          | JP 2002-124737   | 04/26/2002                     | SANYO ELECTRIC CO LTD                              |  | JAPAN (w/English Abstract) |    |
|                     |          | JP 2002-299768   | 10/11/2002                     | MATSUSHITA ELECTRIC IND CO LTD                     |  | JAPAN (w/English Abstract) |    |
|                     |          | JP 2001-57481  | 02/27/2001                     | NICHIA CHEM IND LTD                                |  | JAPAN (w/English Abstract) |    |
|                     |          | JP 11-340580   | 12/10/1999                     | FUJITSU LTD  |  | JAPAN (w/English Abstract) |    |
|                     |          | JP 10-294529   | 11/4/1998                      | TOSHIBA CORP.                                      |  | JAPAN (w/English Abstract) |    |

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |
|---------------------|----------|---|
| LS                  |          | T. Asano, et al. "High-power 400-nm-band AlGaInN-based laser diodes with low aspect ratio." Applied Physics Letters, Volume 80, Number 19, May 13, 2002, pp.3497-3499   |
|                     |          | Nishinaga Tatau, "Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor." Department of Electronic Engineering, Graduate School of Engineering, Volume 21, No. 6, pp. 320-325, 2000                                     |
|                     |          | Takashi Mizuno, et al. "High power Blue-violet Laser Diodes." The Institute of Electronics, Information and Communication Engineers, Technical Report of IEICE, ED2002-112, LQE2002-87 (2002-08), pp. 63-68   |
|                     |          | H. Amano, et al. "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986, pp. 353-355  |

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.